Spread Spectrum Clock Generator MB88152A

MB88152A-100/101/102/110/111/112

DESCRIPTION

MB88152A is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary radiation noise (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator. It corresponds to both of the center spread which modulates input frequency as Middle Centered and down spread which modulates so as not to exceed input frequency.

FEATURES

- Input frequency : 16.6 MHz to 134 MHz
- Output frequency : 16.6 MHz to 134 MHz
- Modulation rate : $\pm 0.5\%$, $\pm 1.5\%$ (Center spread), -1.0%, -3.0% (Down spread)
- Equipped with oscillation circuit: Range of oscillation 16.6 MHz to 48 MHz
- Modulation clock output Duty : 40% to 60%
- Modulation clock Cycle-Cycle Jitter : Less than 100 ps
- Low current consumption by CMOS process : 5 mA (24 MHz : Typ-sample, no load)
- Power supply voltage : 3.3 V \pm 0.3 V
- Operating temperature : $-40 \degree C$ to $+85 \degree C$
- Package : SOP 8-pin

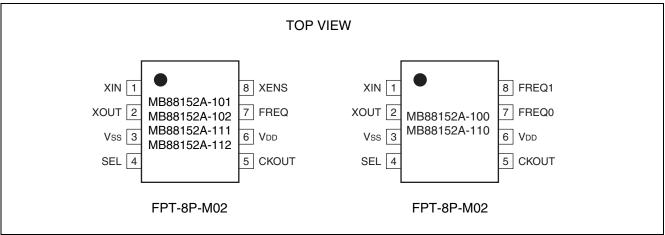


■ PRODUCT LINE-UP

MB88152A has three kinds of input frequency, and two kinds of modulation type (center/down spread), total six line-ups.

Product	Input/Output Frequency	Modulation type	Modulation enable pin
MB88152A-100	16.6 MHz to 134 MHz		No
MB88152A-101	16.6 MHz to 67 MHz	Down spread	Yes
MB88152A-102	40 MHz to 134 MHz		165
MB88152A-110	16.6 MHz to 134 MHz		No
MB88152A-111	16.6 MHz to 67 MHz	Center spread	Yes
MB88152A-112	40 MHz to 134 MHz		Tes

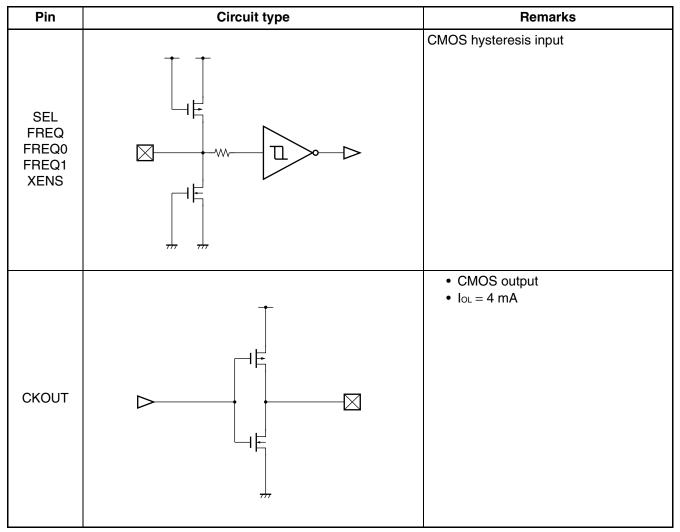
■ PIN ASSIGNMENT



■ PIN DESCRIPTION

Pin name	I/O	Pin no.	Description
XIN	I	1	Crystal resonator connection pin/clock input pin
XOUT	0	2	Crystal resonator connection pin
Vss		3	GND pin
SEL	I	4	Modulation rate setting pin
CKOUT	0	5	Modulated clock output pin
Vdd		6	Power supply voltage pin
FREQ/FREQ0	ļ	7	Frequency setting pin
XENS/FREQ1	I	8	Modulation enable setting pin/frequency setting pin

■ I/O CIRCUIT TYPE



Note : For XIN and XOUT pins, refer to "■OSCILLATION CIRCUIT".

HANDLING DEVICES

Preventing Latch-up

A latch-up can occur if, on this device, (a) a voltage higher than V_{DD} or a voltage lower than V_{SS} is applied to an input or output pin or (b) a voltage higher than the rating is applied between V_{DD} and V_{SS} . The latch-up, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Unused output pin should be opened.

The attention when the external clock is used

Input the clock to XIN pin, and XOUT pin should be opened when you use the external clock.

Please pay attention so that an overshoot and an undershoot do not occur to an input clock of XIN pin.

Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

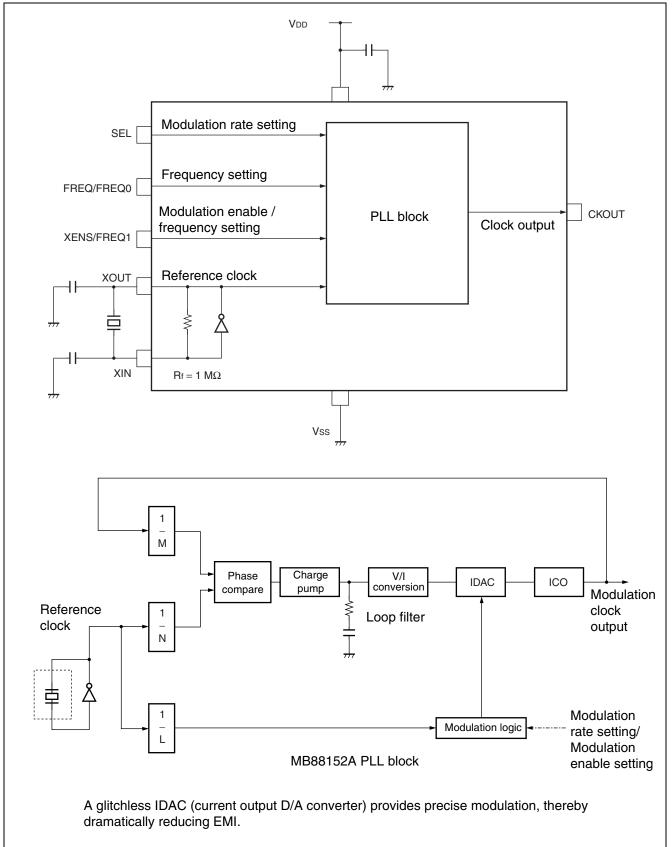
We recommend connecting electrolytic capacitor (about 10 μ F) and the ceramic capacitor (about 0.01 μ F) in parallel between V_{SS} and V_{DD} near the device, as a bypass capacitor.

Oscillation Circuit

Noise near the XIN and XOUT pins may cause the device to malfunction. Design printed circuit boards so that electric wiring of XIN or XOUT pin and resonator (or ceramic oscillator) do not intersect other wiring.

Design the printed circuit board that surrounds the XIN and XOUT pins with ground.

BLOCK DIAGRAM



■ PIN SETTING

When changing the pin setting, the stabilization wait time for the modulation clock is required. The stabilization wait time for the modulation clock takes the maximum value of Lock-Up time in "■ ELECTRICAL CHARACTER-ISTICS • AC characteristics Lock-Up time".

Modulation enable setting

XENS	Modulation				
L	Modulation MB88152A-101, 102, 111, 112				
Н	No modulation	MD00132A-101, 102, 111, 112			

Note : MB88152A-100 and 110 do not have XENS pin.

SEL modulation rate setting

SEL	Modula	Remarks	
1	$\pm 0.5\%$	MB88152A-110, 111, 112	Center spread
L	- 1.0%	MB88152A-100, 101, 102	Down spread
Ц	± 1.5%	MB88152A-110, 111, 112	Center spread
	- 3.0%	MB88152A-100, 101, 102	Down spread

Note : The modulation rate can be changed at the level of the terminal.

Frequency setting

FREQ	Frequency					
	16.6 MHz to 40 MHz	MB88152A-101, 111				
	40 MHz to 80 MHz	MB88152A-102, 112				
L	33 MHz to 67 MHz	MB88152A-101, 111				
	66 MHz to 134 MHz	MB88152A-102, 112				

Note : MB88152A-100 and 110 do not have FREQ pin.

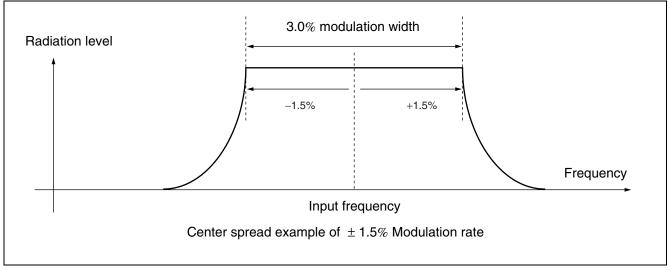
Frequency setting

FREQ1	FREQ0	Frequency				
L	L	16.6 MHz to 40 MHz				
L	Н	33 MHz to 67 MHz	MB88152A-100, 110			
н	L	40 MHz to 80 MHz	MB66152A-100, 110			
Н	Н	66 MHz to 134 MHz				

Note : MB88152A-101, 111, 102 and 112 have neither FREQ0 pin nor FREQ1 pin.

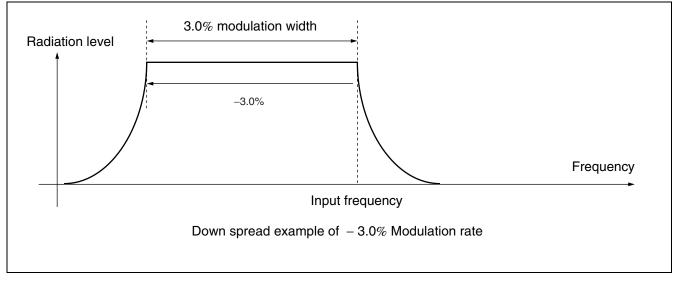
• Center spread

Spectrum is spread (modulated) by centering on the input frequency.



• Down spread

Spectrum is spread (modulated) below the input frequency.

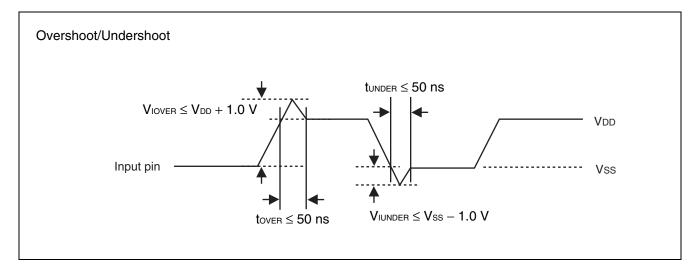


■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rat	Unit		
Parameter	Symbol	Min	Мах	- Unit	
Power supply voltage*	VDD	- 0.5	+ 4.0	V	
Input voltage*	Vi	Vss - 0.5	V _{DD} + 0.5	V	
Output voltage*	Vo	Vss – 0.5	V _{DD} + 0.5	V	
Storage temperature	Тѕт	- 55	+ 125	°C	
Operation junction temperature	TJ	- 40	+ 125	°C	
Output current	lo	- 14	+ 14	mA	
Overshoot	VIOVER	—	V_{DD} + 1.0 (tover \leq 50 ns)	V	
Undershoot	VIUNDER	$V_{\text{SS}} - 1.0$ (tunder ≤ 50 ns)	—	V	

* : The parameter is based on $V_{SS} = 0.0 V$.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



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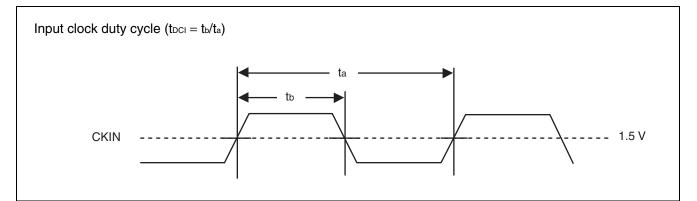
RECOMMENDED OPERATING CONDITIONS

						(Vss =	0.0 V)
Parameter	Symbol	Pin	Conditions		Value		Unit
T diameter	Symbol	FIII	Conditions	Min	Тур	Max	Unit
Power supply voltage	VDD	Vdd	—	3.0	3.3	3.6	V
		SEL, FREQ/FREQ0, XENS/FREQ1	_	$V_{\text{DD}} imes 0.8$	_	V _{DD} + 0.3	v
"H" level input voltage	Vін	XIN	Input through rate 3 V / ns 16.6 MHz to 100 MHz	$V_{\text{DD}} imes 0.8$		V _{DD} + 0.3	v
			Input through rate 3 V / ns 100 MHz to 134 MHz	$V_{\text{DD}} imes 0.9$	_	V _{DD} + 0.3	V
"L" level input voltage		SEL, FREQ/FREQ0, XENS/FREQ1	_	Vss	_	$V_{\text{DD}} \times 0.2$	v
			Input through rate 3 V / ns 16.6 MHz to 100 MHz	Vss	_	V _{DD} + 0.2	v
		AIN	Input through rate 3 V / ns 100 MHz to 134 MHz	Vss	_	V _{DD} + 0.1	v
Input clock	t = a:	XIN	16.6 MHz to 100 MHz	40	50	60	07
duty cycle	tDCI		100 MHz to 134 MHz	45	50	55	%
Operating temperature	Та		—	-40		+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.



■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

$(1a = -40 \text{ C to } + 65 \text{ C}, \text{ Vbb} = 5.3 \text{ V} \pm 0.3 \text{ V}, \text{ Vss} = 0.0 \text{ V})$							
Parameter	Sym-	Pin	Pin Conditions	Value			Unit
Falailletei	bol	FIII	Conditions	Min	Тур	Max	Unit
Power supply current	lcc	Vdd	24 MHz output No load capacitance	—	5.0	7.0	mA
Output voltage	Vон	СКОИТ	"H" level output Іон = – 4 mA	$V_{\text{DD}}-0.5$		Vdd	V
	Vol	CROOT	"L" level output Io∟ = 4 mA	Vss		0.4	V
Output impedance	Zo	CKOUT	16.6 MHz to 134 MHz	—	45	_	Ω
Input capacitance	Cin	XIN, SEL, FREQ/ FREQ0, XENS/ FREQ1	$Ta = +25 \ ^{\circ}C$ $V_{DD} = V_{I} = 0.0 \ V$ $f = 1 \ MHz$	_	_	16	pF
Load capacitance			16.6 MHz to 67 MHz	—		15	
	C∟	CKOUT	67 MHz to 100 MHz	—		10	pF
			100 MHz to 134 MHz			7	

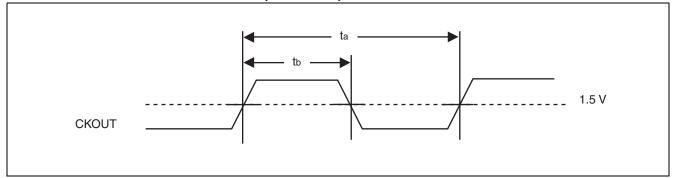
(Ta = -40 °C to + 85 °C, V_{DD} = 3.3 V \pm 0.3 V, V_{SS} = 0.0 V)

• AC Characteristics

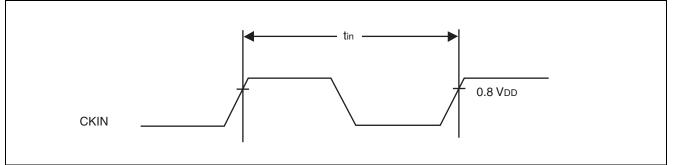
Parameter	Sym-	Pin	Conditions	Value			Unit
raiameter	bol		Conditions	Min	Тур	Мах	Onit
Oscillation frequency	fx	XIN,	Fundamental oscillation	16.6	—	40	MHz
	IX	XOUT	3rd over tone	40		48	
			MB88152A-100, 110	16.6		134	
Input frequency	fin	XIN	MB88152A-101, 111	16.6		67	MHz
			MB88152A-102, 112	40		134	
			MB88152A-100, 110	16.6		134	
Output frequency	fouт	CKOUT	MB88152A-101, 111	16.6		67	MHz
			MB88152A-102, 112	40		134	
Output slew rate	SR	СКОИТ	0.4 V to 2.4 V Load capacitance 15 pF	0.4		4.0	V/ns
Output clock duty cycle	tDCC	CKOUT	1.5 V	40		60	%
Modulation cycle	fмор	CKOUT	—		12.5		kHz
Lock-Up time	t∟ĸ	CKOUT	—		2	5	ms
Cycle-cycle jitter	tjc	СКОИТ	No load capacitance, $Ta = +25 \ ^{\circ}C,$ $V_{DD} = 3.3 \ V,$ Standard deviation σ	_		100	ps

(Ta = -40 °C to $\,+\,85$ °C, V_{DD} = 3.3 V $\pm\,0.3$ V, Vss = 0.0 V)

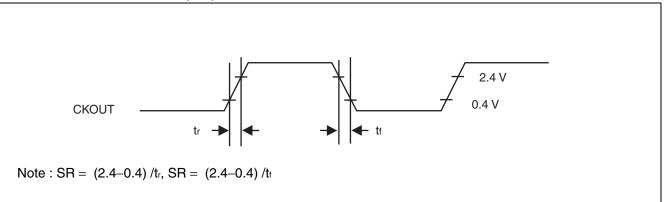
■ OUTPUT CLOCK DUTY CYCLE (t_{DCC} = t_b/t_a)



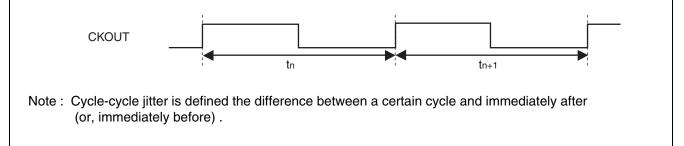
■ INPUT FREQUENCY (fin = 1/tin)



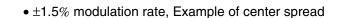
■ OUTPUT SLEW RATE (SR)

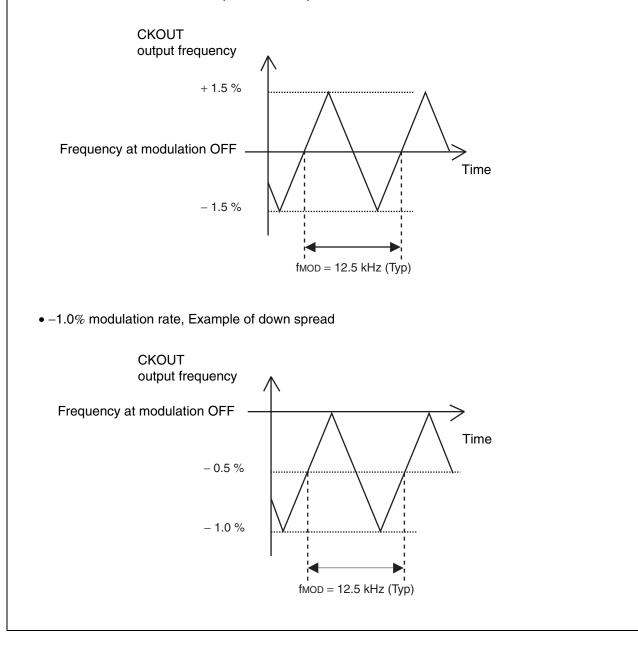


$\blacksquare CYCLE-CYCLE JITTER (t_{JC} = | t_n - t_{n+1} |)$

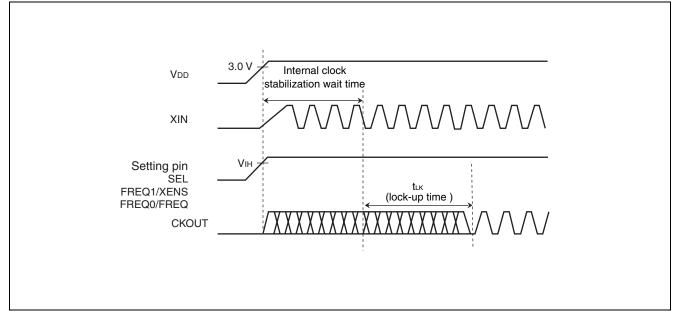


■ MODULATION WAVEFORM

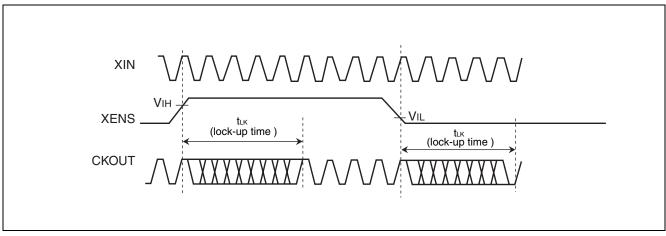




LOCK-UP TIME



If the setting pin is fixed at the "H" or "L" level, the maximum time after the power is turned on until the set clock signal is output from CKOUT pin is (the stabilization wait time of input clock to XIN pin) + (the lock-up time "tLK"). For the input clock stabilization time, check the characteristics of the resonator or oscillator used.



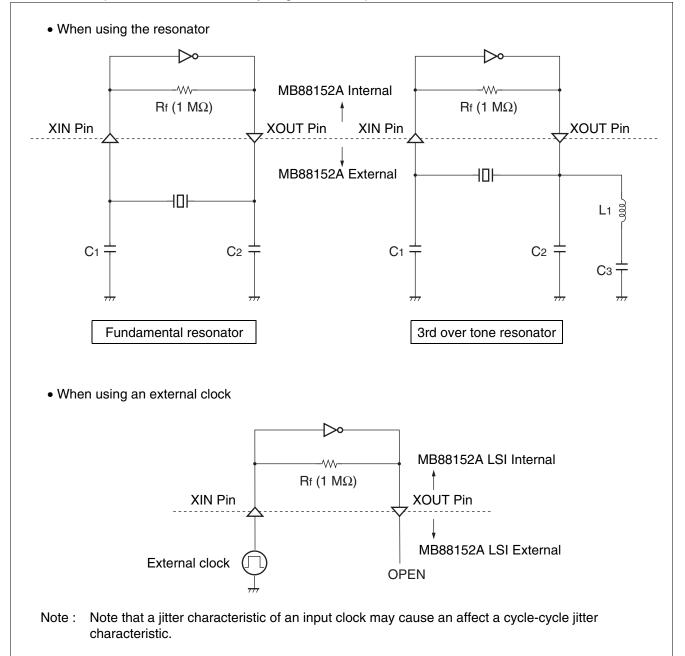
For modulation enable control using the XENS pin during normal operation, the set clock signal is output from CKOUT pin at most the lock-up time (t_{LK}) after the level at the XENS pin is determined.

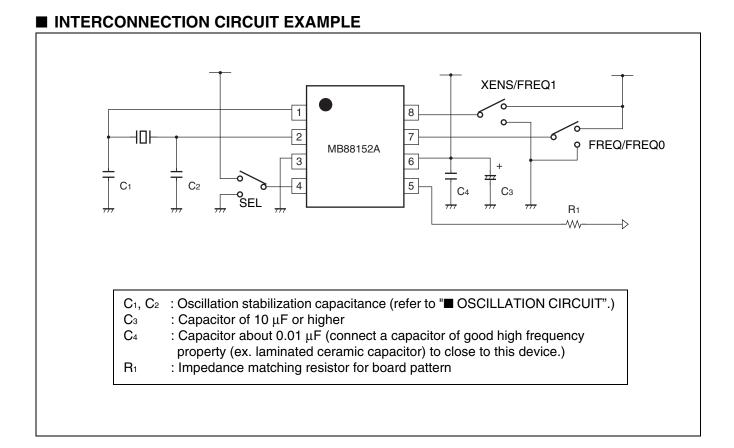
Note : When the pin setting is changed, the CKOUT pin output clock stabilization time is required. Until the output clock signal becomes stable, the output frequency, output clock duty cycle, modulation period, and cycle-cycle jitter cannot be guaranteed. It is therefore advisable to perform processing such as cancelling a reset of the device at the succeeding stage after the lock-up time.

OSCILLATION CIRCUIT

The left side of figures below shows the connection example about general resonator. The oscillation circuit has the built-in feedback resistance (1 M Ω). The value of capacity (C₁ and C₂) is required adjusting to the most suitable value of an individual resonator.

The right side of figures below shows the example of connecting for the 3rd over-tone resonator. The value of capacity (C_1 , C_2 and C_3) and inductance (L_1) is needed adjusting to the most suitable value of an individual resonator. The most suitable value is different by individual resonator. Please refer to the resonator manufacturer which you use for the most suitable value. When an external clock is used (the resonator is not used), input the clock to XIN pin and do not connect anything with XOUT pin.



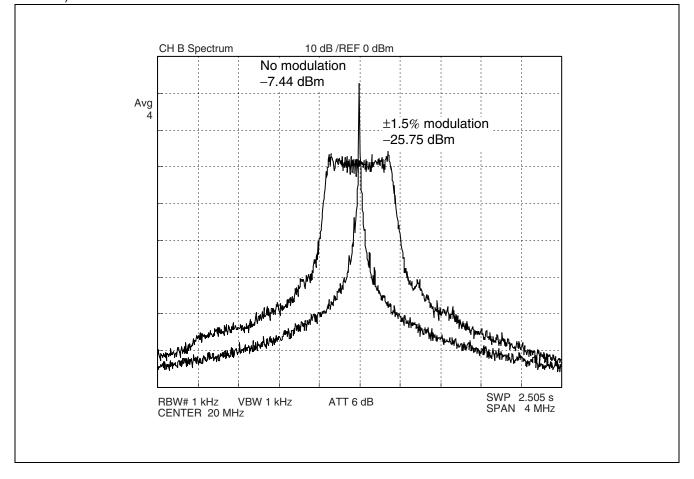


■ EXAMPLE CHARACTERISTICS

The condition of the examples of the characteristics is shown as follows : Input frequency = 20 MHz (Output frequency = 20 MHz : Use for MB88152A-111)

Power-supply voltage = 3.3 V, None load capacity, Modulation rate = $\pm 1.5\%$ (center spread) .

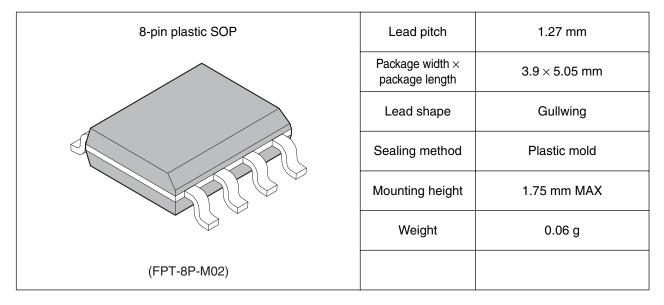
Spectrum analyzer HP4396B is connected with CKOUT. The result of the measurement with, RBW = 1 kHz (ATT use for -6 dB).

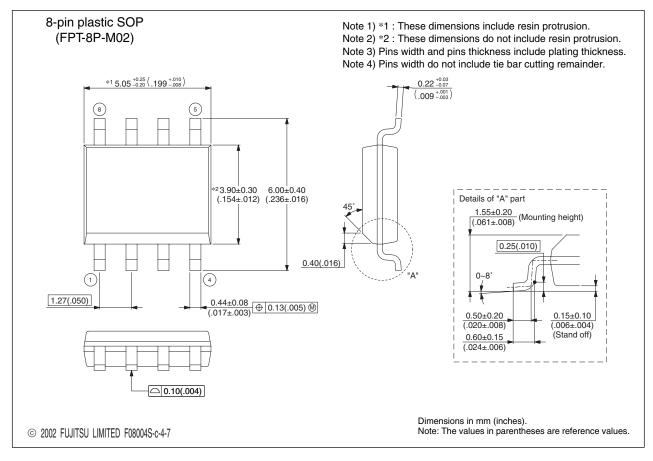


■ ORDERING INFORMATION

Part number	Input/Output Frequency	Modulation type	Modulation enable pin	Package	Remarks
MB88152APNF-G-100-JNE1	16.6 MHz to 134 MHz	Down spread	No		
MB88152APNF-G-101-JNE1	16.6 MHz to 67 MHz	Down spread	Yes		
MB88152APNF-G-102-JNE1	40 MHz to 134 MHz	Down spread	Yes	8-pin plastic SOP	
MB88152APNF-G-110-JNE1	16.6 MHz to 134 MHz	Center spread	No	(FPT-8P-M02)	
MB88152APNF-G-111-JNE1	16.6 MHz to 67 MHz	Center spread	Yes		
MB88152APNF-G-112-JNE1	40 MHz to 134 MHz	Center spread	Yes		
MB88152APNF-G-100-JN-EFE1	16.6 MHz to 134 MHz	Down spread	No		
MB88152APNF-G-101-JN-EFE1	16.6 MHz to 67 MHz	Down spread	Yes		
MB88152APNF-G-102-JN-EFE1	40 MHz to 134 MHz	Down spread	Yes	8-pin plastic SOP	Emboss
MB88152APNF-G-110-JN-EFE1	16.6 MHz to 134 MHz	Center spread	No	(FPT-8P-M02)	taping (EF type)
MB88152APNF-G-111-JN-EFE1	16.6 MHz to 67 MHz	Center spread	Yes		
MB88152APNF-G-112-JN-EFE1	40 MHz to 134 MHz	Center spread	Yes		
MB88152APNF-G-100-JN-ERE1	16.6 MHz to 134 MHz	Down spread	No		
MB88152APNF-G-101-JN-ERE1	16.6 MHz to 67 MHz	Down spread	Yes		
MB88152APNF-G-102-JN-ERE1	40 MHz to 134 MHz	Down spread	Yes	8-pin plastic SOP	Emboss
MB88152APNF-G-110-JN-ERE1	16.6 MHz to 134 MHz	Center spread	No	(FPT-8P-M02)	taping (ER type)
MB88152APNF-G-111-JN-ERE1	16.6 MHz to 67 MHz	Center spread	Yes		,
MB88152APNF-G-112-JN-ERE1	40 MHz to 134 MHz	Center spread	Yes		

PACKAGE DIMENSION





Please confirm the latest Package dimension by following URL. http://edevice.fujitsu.com/fj/DATASHEET/ef-ovpklv.html

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